Zener Diodes, 24 and 40 Watt Peak Power

SOT-23 Dual Common Anode Zeners

These dual monolithic silicon Zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Features

- SOT–23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Standard Zener Breakdown Voltage Range 5.6 V to 47 V
- Peak Power 24 or 40 W @ 1.0 ms (Unidirectional), per Figure 6 Waveform
- ESD Rating:
 - Class 3B (> 16 kV) per the Human Body Model
 - Class C (> 400 V) per the Machine Model
- ESD Rating of IEC61000-4-2 Level 4, ±30 kV Contact Discharge
- Maximum Clamping Voltage @ Peak Pulse Current
- Low Leakage < 5.0 μA
- Flammability Rating UL 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Mechanical Characteristics

CASE: Void-free, transfer-molded, thermosetting plastic case

FINISH: Corrosion resistant finish, easily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

260°C for 10 Seconds

Package designed for optimal automated board assembly Small package size for high density applications Available in 8 mm Tape and Reel

Use the Device Number to order the 7 inch/3,000 unit reel. Replace the "T1" with "T3" in the Device Number to order the 13 inch/10,000 unit reel.

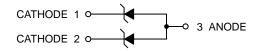


ON Semiconductor®

www.onsemi.com



SOT-23 CASE 318 STYLE 12



MARKING DIAGRAM



XXX = Specific Device Code

M = Date Code

■ = Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the table on page 3 of this data sheet.

MAXIMUM RATINGS

Rati	Symbol	Value	Unit	
Peak Power Dissipation @ 1.0 ms (Note 1) @ T _L ≤ 25°C	MMBZ5V6ALT1G thru MMBZ9V1ALT1G MMBZ12VALT1G thru MMBZ47VALT1G	P _{pk}	24 40	W
Total Power Dissipation on FR-5 Board (Note @ T _A = 25°C Derate above 25°C	e 2)	P _D	225 1.8	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	556	°C/W	
Total Power Dissipation on Alumina Substrate @ T _A = 25°C Derate above 25°C	e (Note 3)	P _D	300 2.4	mW mW/°C
Thermal Resistance Junction-to-Ambient		$R_{ heta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to +150	°C	
Lead Solder Temperature – Maximum (10 Se	TL	260	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Non-repetitive current pulse per Figure 6 and derate above $T_A = 25$ °C per Figure 7.
- 2. $FR-5 = 1.0 \times 0.75 \times 0.62$ in.
- 3. Alumina = $0.4 \times 0.3 \times 0.024$ in, 99.5% alumina.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBZ5V6ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZ5V6ALT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZ5V6ALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBZ6VxALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZ6VxALT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZ6VxALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBZ9V1ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZ9V1ALT13G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBZxxVALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZxxVALT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZxxVALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZMMBZxxVALT3G*	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZMMBZxxVTALT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}Other voltages may be available upon request.

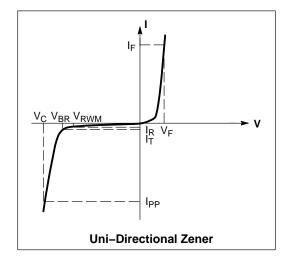
^{*}SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
Ι _Τ	Test Current
ΘV_{BR}	Maximum Temperature Coefficient of V _{BR}
I _F	Forward Current
V _F	Forward Voltage @ I _F
Z _{ZT}	Maximum Zener Impedance @ I _{ZT}
I _{ZK}	Reverse Current
Z _{ZK}	Maximum Zener Impedance @ I _{ZK}



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

 $(V_F = 0.9 \text{ V Max } @ I_F = 10 \text{ mA}) (5\% \text{ Tolerance})$

24 WATTS

				Breakdown Voltage				ax Zene ance (N		V _C (Not	D I _{PP} (e 6)		
	Device	V _{RWM}	I _R @ V _{RWM}	V _{BF}	(Note 4)	(V)	@ I _T	Z _{ZT} @ I _{ZT}	Z _{ZK} (@ I _{ZK}	v _c	I _{PP}	ΘV _{BR}
Device*	Marking	Volts	μΑ	Min	Nom	Max	mA	Ω	Ω	mA	٧	Α	mV/°C
MMBZ5V6ALT1G/T3G	5A6	3.0	5.0	5.32	5.6	5.88	20	11	1600	0.25	8.0	3.0	1.26
MMBZ6V2ALT1G	6A2	3.0	0.5	5.89	6.2	6.51	1.0	1	-	-	8.7	2.76	2.80
MMBZ6V8ALT1G	6A8	4.5	0.5	6.46	6.8	7.14	1.0	1	-	-	9.6	2.5	3.4
MMBZ9V1ALT1G	9A1	6.0	0.3	8.65	9.1	9.56	1.0	_	_	_	14	1.7	7.5

 $(V_F = 0.9 \text{ V Max } @ I_F = 10 \text{ mA}) (5\% \text{ Tolerance})$

40 WATTS

			I _R @		Breakdown Voltage			V _C @ I _{PF}		
	Device	V _{RWM}	V _{RWM}	V _{BF}	(Note 4)	(V)	@ I _T	V _C	I _{PP}	ΘV_{BR}
Device*	Marking	Volts	nA	Min	Nom	Max	mA	٧	Α	mV/°C
MMBZ12VALT1G	12A	8.5	200	11.40	12	12.60	1.0	17	2.35	7.5
MMBZ15VALT1G	15A	12	50	14.25	15	15.75	1.0	21	1.9	12.3
MMBZ16VALT1G	16A	13	50	15.20	16	16.80	1.0	23	1.7	13.8
MMBZ18VALT1G	18A	14.5	50	17.10	18	18.90	1.0	25	1.6	15.3
MMBZ20VALT1G	20A	17	50	19.00	20	21.00	1.0	28	1.4	17.2
MMBZ27VALT1G/T3G	27A	22	50	25.65	27	28.35	1.0	40	1.0	24.3
MMBZ33VALT1G	33A	26	50	31.35	33	34.65	1.0	46	0.87	30.4
MMBZ47VALT1G	47A	38	50	44.65	47	49.35	1.0	54	0.74	43.1

 $(V_F = 0.9 \text{ V Max } @ I_F = 10 \text{ mA}) (2\% \text{ Tolerance})$

40 WATTS

			I _R @	Breakdown Voltage			9	V _C @ I _{PF}	(Note 6)	
	Device	V _{RWM}	V _{RWM}	V _{BR} (Note 4) (V)		@ I _T	V _C	I _{PP}	ΘV _{BR}	
Device*	Marking	Volts	nA	Min	Nom	Max	mA	V	Α	mV/°C
MMBZ16VTALT1G	16T	13	50	15.68	16	16.32	1.0	23	1.7	13.8
MMBZ47VTALT1G	47T	38	50	46.06	47	47.94	1.0	54	0.74	43.1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.
 Z_{ZT} and Z_{ZK} are measured by dividing the AC voltage drop across the device by the AC current applied. The specified limits are for I_{Z(AC)} = 0.1 I_{Z(DC)}, with the AC frequency = 1.0 kHz.
 Surge current waveform per Figure 6 and derate per Figure 7

^{*} Include SZ-prefix devices where applicable.

TYPICAL CHARACTERISTICS

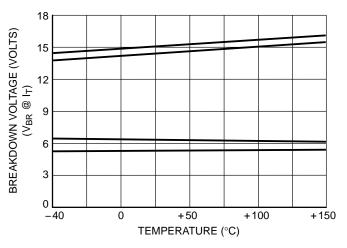


Figure 1. Typical Breakdown Voltage versus Temperature

(Upper curve for each voltage is bidirectional mode, lower curve is unidirectional mode)

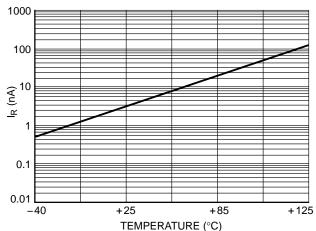


Figure 2. Typical Leakage Current versus Temperature

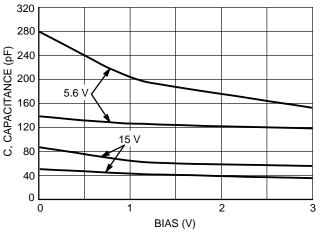


Figure 3. Typical Capacitance versus Bias Voltage
(Upper curve for each voltage is unidirectional mode,
lower curve is bidirectional mode)

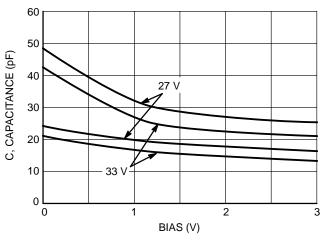


Figure 4. Typical Capacitance versus Bias Voltage (Upper curve for each voltage is unidirectional mode, lower curve is bidirectional mode)

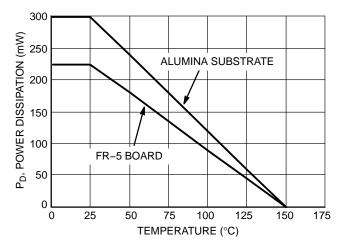


Figure 5. Steady State Power Derating Curve

TYPICAL CHARACTERISTICS

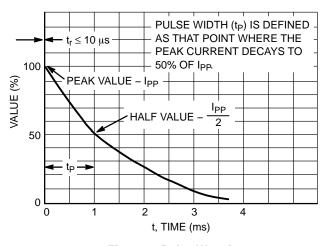


Figure 6. Pulse Waveform

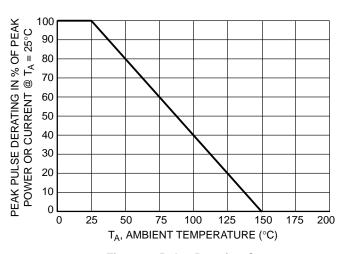


Figure 7. Pulse Derating Curve

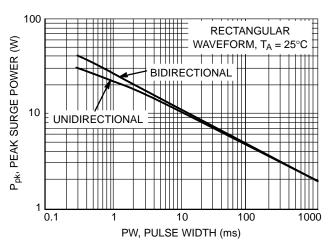


Figure 8. Maximum Non-repetitive Surge Power, P_{pk} versus PW

Power is defined as $V_{RSM}\,x\,I_Z(pk)$ where V_{RSM} is the clamping voltage at $I_Z(pk).$

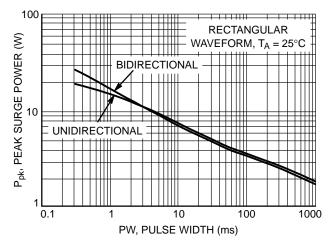


Figure 9. Maximum Non-repetitive Surge Power, Ppk(NOM) versus PW

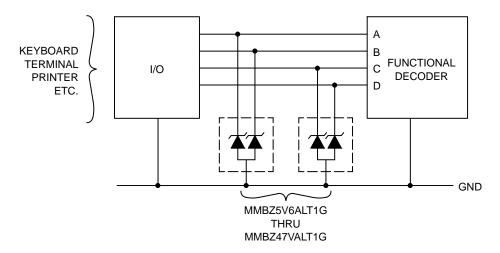
Power is defined as $V_Z(NOM) \times I_Z(pk)$ where $V_Z(NOM)$ is the nominal Zener voltage measured at the low test current used for voltage classification.

TYPICAL COMMON ANODE APPLICATIONS

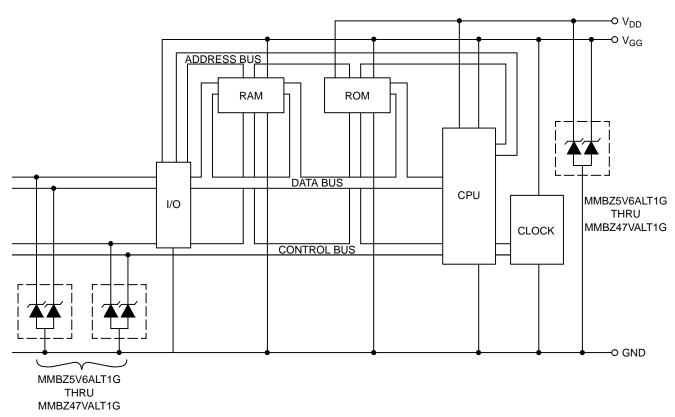
A dual junction common anode design in a SOT-23 package protects two separate lines using only one package. This adds flexibility and creativity to PCB design especially

when board space is at a premium. Two simplified examples of ESD applications are illustrated below.

Computer Interface Protection



Microprocessor Protection







SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.	
Α	0.89	1.00	1.11	0.035	0.039	0.044	
A1	0.01	0.06	0.10	0.000	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.017	0.020	
С	0.08	0.14	0.20	0.003	0.006	0.008	
D	2.80	2.90	3.04	0.110	0.114	0.120	
Ε	1.20	1.30	1.40	0.047	0.051	0.055	
e	1.78	1.90	2.04	0.070	0.075	0.080	
L	0.30	0.43	0.55	0.012	0.017	0.022	
L1	0.35	0.54	0.69	0.014	0.021	0.027	
HE	2.10	2.40	2.64	0.083	0.094	0.104	
Т	0*		10°	0*		10°	

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Rep Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2				

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2			

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMi., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer p

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative